

### **ZVP3306A Information**



For Reference Only

Part Number ZVP3306A

Manufacturer Diodes Incorporated

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

**Description** MOSFET P-CH 60V 160MA TO92-3 **Package** TO-226-3, TO-92-3 (TO-226AA)

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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# **Certified Quality**

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# **ZVP3306A Specifications**

Manufacturer Part Number         ZVP3306A           Manufacturer         Diodes Incorporated           Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-226-3, TO-92-3 (TO-226AA)           Series         -           FET Type         P-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         60V           Current - Continuous Drain (Id) @ 25°C         160mA (Ta)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         3.5V @ ImA           Gate Charge (Qg) (Max) @ Vgs         -           Input Capacitance (Ciss) (Max) @ Vds         50pF @ 18V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         625mW (Ta)           Rds On (Max) @ Id, Vgs         14 Ohm @ 200mA, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-92-3           Package / Case         TO-226-3, TO-92-3 (TO-226AA)           Report errors?		
Category  Discrete Semiconductor Products  Transistors - FETs, MOSFETs - Single  Package  TO-226-3, TO-92-3 (TO-226AA)  Series  - FET Type  P-Channel  Technology  MOSFET (Metal Oxide)  four - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  ### 20V  ### 31A On (Max)  ### 32 On (Max) @ Id, Vgs  ### 33 On (Max) @ Id, Vgs  ### 34 On (Max) @ Id, Vgs  ### 35 On (Max) @ Id, Vgs  ### 36 On (Max) @ Id, Vgs  ### 37 On (Max) @ Id, Vgs  ### 38 On (Max) @ Id, Vgs  ### 39 On (Max) @ Id, Vgs  ### 30 On (Max) @ Id, Vgs  ### 30 On (Max) @ Id, Vgs  ### 31 On (Max) @ Id, Vgs  ### 31 On (Max) @ Id, Vgs  ### 32 On (Max) @ Id, Vgs  ### 31 On (Max) @ Id, Vgs  ### 32 On (Max) @ Id, Vgs  ### 31 On (Max) @ Id, Vgs  ### 32 On (Max) @ Id, Vgs  ### 31 On (Max) @ Id, Vgs  ### 31 On (Max) @ Id, Vgs  ### 32 On (Max) @ Id, Vgs  ### 33 On (Max) @ Id, Vgs  ### 34 On (Max) @ Id, Vgs  ### 35 On (Max) @ Id, Vgs  ### 35 On (Max) @ Id, Vgs  ### 36 On (Max) @ Id, Vgs  ### 37 On (Max) @ Id, Vgs  ### 37 On (Max) @ Id, Vgs  ### 37 On (Max) @ Id, Vgs  ### 38 On (Max) @ Id, Vgs  ### 38 On (Max) @ Id, Vgs  ### 38 On (Max) @ Id, Vgs  ### 37 On (Max) @ Id, Vgs  ### 37 On (Max) @ Id, Vgs  ### 38 On (Max) @ Id, Vgs  ### 37 On (Max) @ Id, Vgs  ### 38 On (Max) @ Id, Vgs  ### 39 On (Max) @ Id, Vgs  ### 30 On (Max) @ Id	Manufacturer Part Number	ZVP3306A
Package         TO-226-3, TO-92-3 (TO-226AA)           Series         -           FET Type         P-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         60V           Current - Continuous Drain (Id) @ 25°C         160mA (Ta)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         3.5V @ 1mA           Gate Charge (Qg) (Max) @ Vgs         -           Input Capacitance (Ciss) (Max) @ Vds         50pF @ 18V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         625mW (Ta)           Rds On (Max) @ Id, Vgs         14 Ohm @ 200mA, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-92-3           Package / Case         TO-226-A, TO-92-3 (TO-226AA)	Manufacturer	Diodes Incorporated
Package         TO-226-3, TO-92-3 (TO-226AA)           Series         -           FET Type         P-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         60V           Current - Continuous Drain (Id) @ 25°C         160mA (Ta)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         3.5V @ 1mA           Gate Charge (Qg) (Max) @ Vgs         -           Input Capacitance (Ciss) (Max) @ Vds         50pF @ 18V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         625mW (Ta)           Rds On (Max) @ Id, Vgs         14 Ohm @ 200mA, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-92-3           Package / Case         TO-226-3, TO-92-3 (TO-226AA)	Category	Discrete Semiconductor Products
Series         -           FET Type         P-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         60V           Current - Continuous Drain (Id) @ 25°C         160mA (Ta)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         3.5V @ 1mA           Gate Charge (Qg) (Max) @ Vgs         -           Input Capacitance (Ciss) (Max) @ Vds         50pF @ 18V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         625mW (Ta)           Rds On (Max) @ Id, Vgs         14 Ohm @ 200mA, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-92-3 (TO-226AA)		Transistors - FETs, MOSFETs - Single
FET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C160mA (Ta)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id3.5V @ 1mAGate Charge (Qg) (Max) @ Vgs-Input Capacitance (Ciss) (Max) @ Vds50pF @ 18VVgs (Max)±20VFET Feature-Power Dissipation (Max)625mW (Ta)Rds On (Max) @ Id, Vgs14 Ohm @ 200mA, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-92-3Package / CaseTO-226-3, TO-92-3 (TO-226AA)	Package	TO-226-3, TO-92-3 (TO-226AA)
Technology  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  160mA (Ta)  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  **EUV**  FET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  14 Ohm @ 200mA, 10V  Operating Temperature  - 55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-92-3  Package / Case  **To-92-3 (TO-226AA)	Series	-
Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C160mA (Ta)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id3.5V @ 1mAGate Charge (Qg) (Max) @ Vgs-Input Capacitance (Ciss) (Max) @ Vds50pF @ 18VVgs (Max)±20VFET Feature-Power Dissipation (Max)625mW (Ta)Rds On (Max) @ Id, Vgs14 Ohm @ 200mA, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-92-3Package / CaseTO-226-3, TO-92-3 (TO-226AA)	FET Type	P-Channel
Current - Continuous Drain (Id) @ 25°C 160mA (Ta)  Drive Voltage (Max Rds On, Min Rds On) 10V  Vgs(th) (Max) @ Id 3.5V @ 1mA  Gate Charge (Qg) (Max) @ Vgs -  Input Capacitance (Ciss) (Max) @ Vds 50pF @ 18V  Vgs (Max) ±20V  FET Feature -  Power Dissipation (Max) 625mW (Ta)  Rds On (Max) @ Id, Vgs 14 Ohm @ 200mA, 10V  Operating Temperature -55°C ~ 150°C (TJ)  Mounting Type Through Hole  Supplier Device Package TO-92-3  Package / Case TO-226-3, TO-92-3 (TO-226AA)	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  3.5V @ 1mA  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  14 Ohm @ 200mA, 10V  Operating Temperature  Supplier Device Package  Package / Case  TO-92-3  TO-92-3 (TO-226AA)	Drain to Source Voltage (Vdss)	60V
Vgs(th) (Max) @ Id       3.5V @ 1mA         Gate Charge (Qg) (Max) @ Vgs       -         Input Capacitance (Ciss) (Max) @ Vds       50pF @ 18V         Vgs (Max)       ±20V         FET Feature       -         Power Dissipation (Max)       625mW (Ta)         Rds On (Max) @ Id, Vgs       14 Ohm @ 200mA, 10V         Operating Temperature       -55°C ~ 150°C (TJ)         Mounting Type       Through Hole         Supplier Device Package       TO-92-3         Package / Case       TO-226-3, TO-92-3 (TO-226AA)	Current - Continuous Drain (Id) @ 25°C	160mA (Ta)
Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  14 Ohm @ 200mA, 10V  Operating Temperature  Jenses Supplier Device Package  TO-92-3  Package / Case  TO-226-3, TO-92-3 (TO-226AA)	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  ±20V  FET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  14 Ohm @ 200mA, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-92-3  Package / Case  TO-226-3, TO-92-3 (TO-226AA)	Vgs(th) (Max) @ Id	3.5V @ 1mA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)625mW (Ta)Rds On (Max) @ Id, Vgs14 Ohm @ 200mA, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-92-3Package / CaseTO-226-3, TO-92-3 (TO-226AA)	Gate Charge (Qg) (Max) @ Vgs	-
FET Feature - Power Dissipation (Max) 625mW (Ta) Rds On (Max) @ Id, Vgs 14 Ohm @ 200mA, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92-3 Package / Case TO-226-3, TO-92-3 (TO-226AA)	Input Capacitance (Ciss) (Max) @ Vds	50pF @ 18V
Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  14 Ohm @ 200mA, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-92-3  Package / Case  TO-226-3, TO-92-3 (TO-226AA)	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs14 Ohm @ 200mA, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-92-3Package / CaseTO-226-3, TO-92-3 (TO-226AA)	FET Feature	-
Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-92-3  Package / Case  TO-226-3, TO-92-3 (TO-226AA)	Power Dissipation (Max)	625mW (Ta)
Mounting Type Through Hole Supplier Device Package TO-92-3 Package / Case TO-226-3, TO-92-3 (TO-226AA)	Rds On (Max) @ Id, Vgs	14 Ohm @ 200mA, 10V
Supplier Device Package TO-92-3 Package / Case TO-226-3, TO-92-3 (TO-226AA)	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-226-3, TO-92-3 (TO-226AA)	Mounting Type	Through Hole
	Supplier Device Package	TO-92-3
Report errors?	Package / Case	TO-226-3, TO-92-3 (TO-226AA)
		Report errors?

#### **ZVP3306A Guarantees**



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

### **ZVP3306A Payment Methods**



















### **ZVP3306A Shipping Methods**













If you have any question about ZVP3306A, please do not hesitate to contact us!

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